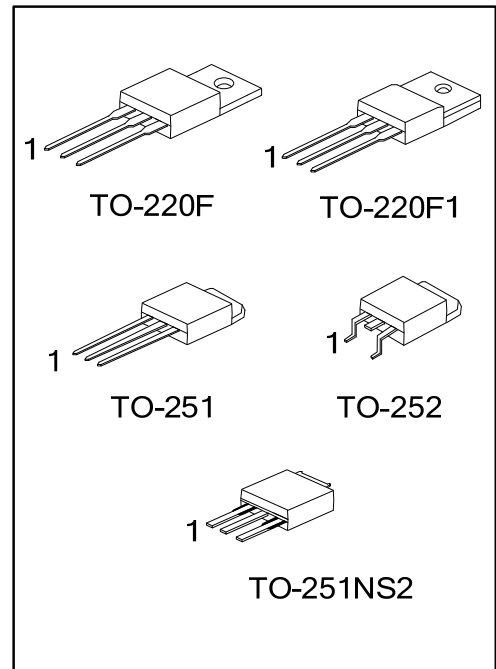
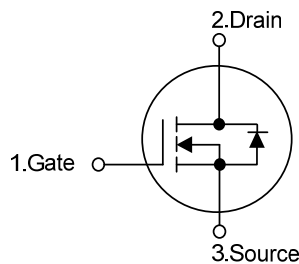


**4N60-HC****Power MOSFET****4A, 600V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **4N60-HC** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} < 2.2 \Omega$ @ $V_{GS} = 10V$, $I_D = 2.0A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

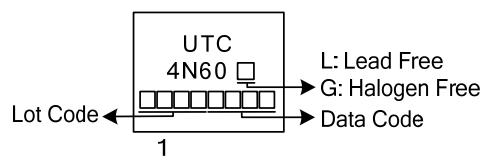
SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N60L-TF1-T	4N60G-TF1-T	TO-220F1	G	D	S	Tube
4N60L-TF3-T	4N60G-TF3-T	TO-220F	G	D	S	Tube
4N60L-TM3-T	4N60G-TM3-T	TO-251	G	D	S	Tube
4N60L-TN3-R	4N60G-TN3-R	TO-252	G	D	S	Tape Reel
4N60L-TMN2-T	4N60G-TMN2-T	TO-251NS2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

4N60G-TF1-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TF3: TO-220F, TM3: TO-251 TN3: TO-252, TMS2: TO-251NS2 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	4	A
Pulsed Drain Current (Note 2)		I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	132	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.4	V/ns
Power Dissipation	TO-220F/TO-220F1	P_D	34	W
	TO-251/TO-252		50	W
	TO-251NS2			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30\text{mH}$, $I_{AS} = 2.97\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F/TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		110	$^\circ\text{C}/\text{W}$
	TO-251NS2			
Junction to Case	TO-220F/TO-220F1	θ_{JC}	3.68	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		2.5	$^\circ\text{C}/\text{W}$
	TO-251NS2			

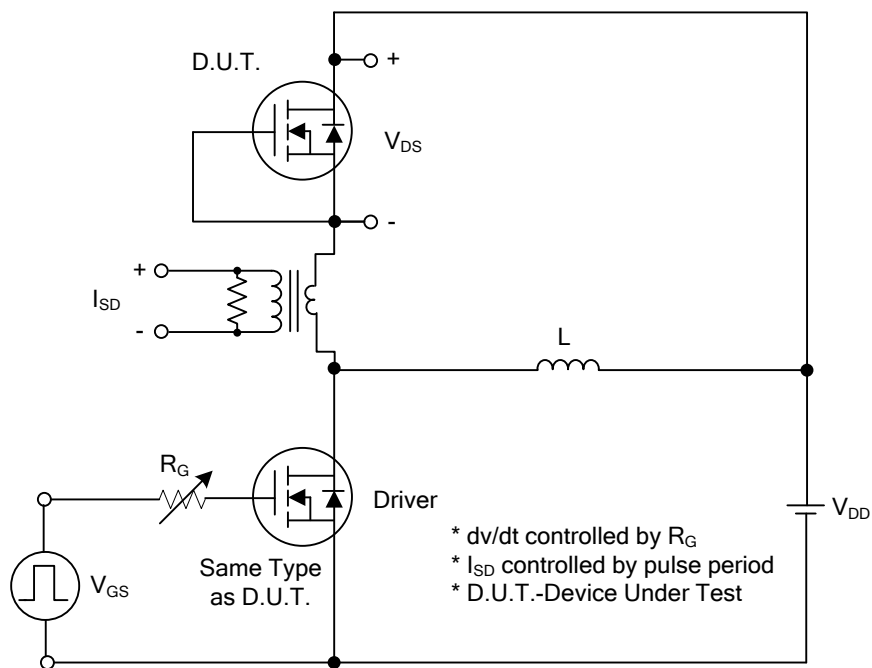
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 2.0A			2.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		551		pF
Output Capacitance		C _{OSS}			186		pF
Reverse Transfer Capacitance		C _{RSS}			66		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =150V, V _{GS} =10V, I _D =5.0A, I _D =100μA (Note 1, 2)		18.3		nC
Gate-Source Charge		Q _{GS}			6.4		nC
Gate-Drain Charge		Q _{GD}			5.6		nC
Turn-On Delay Time (Note 1)		t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =5.0A, R _G =25Ω (Note 1, 2)		11		ns
Turn-On Rise Time		t _R			15		ns
Turn-Off Delay Time		t _{D(OFF)}			60		ns
Turn-Off Fall Time		t _F			26		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				4	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				16	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =4.0A , V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _S =4.0A , V _{GS} =0V di/dt=100A/μs		285		ns
Body Diode Reverse Recovery Charge		Q _{rr}			1.54		μC

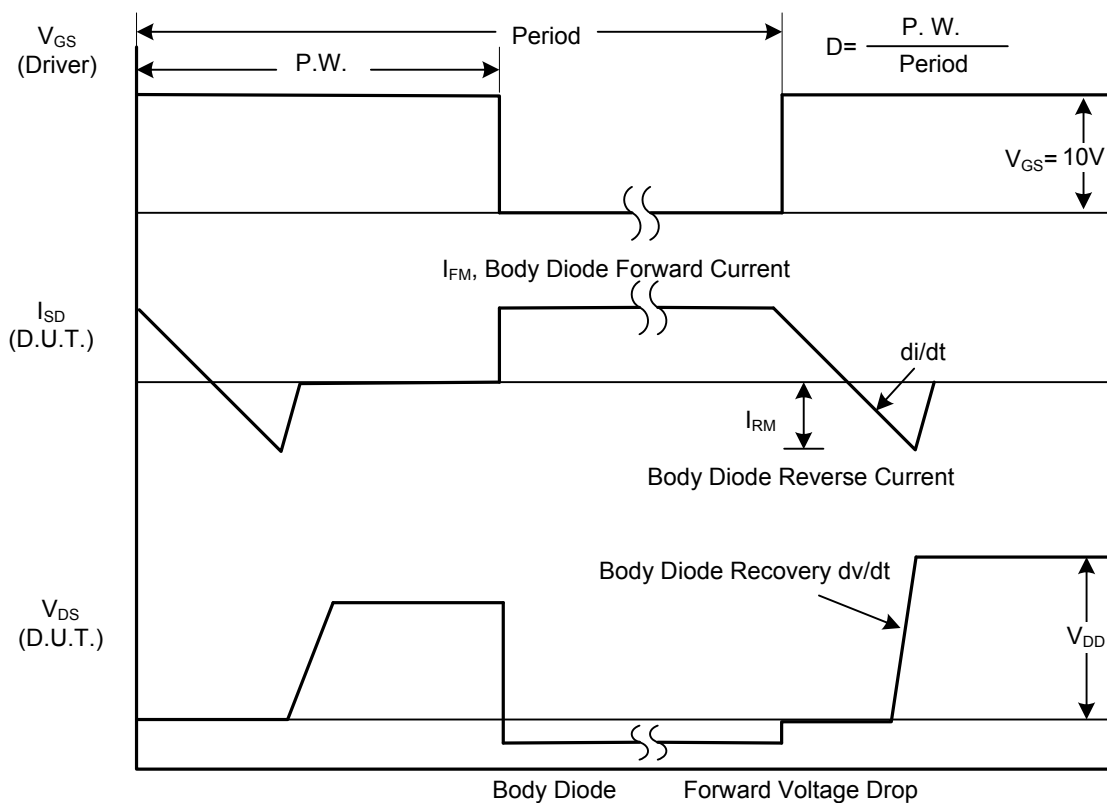
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

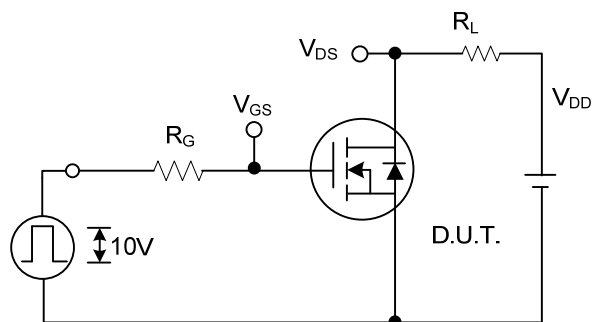


Peak Diode Recovery dv/dt Test Circuit

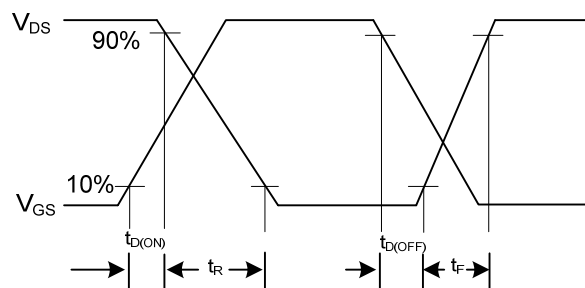


Peak Diode Recovery dv/dt Waveforms

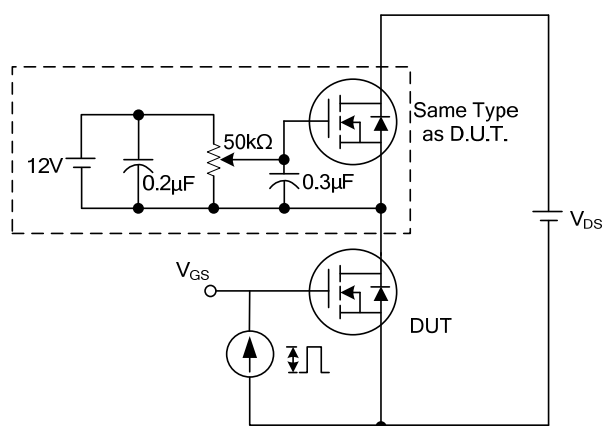
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



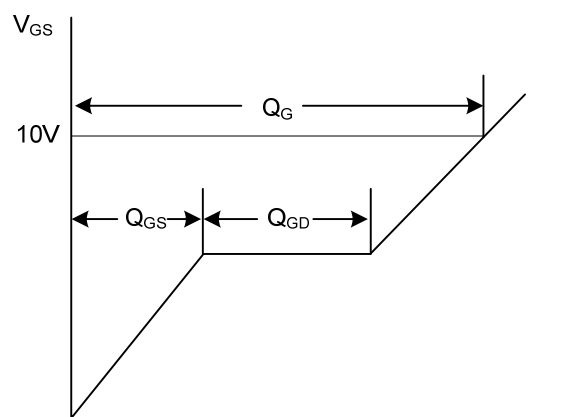
Switching Test Circuit



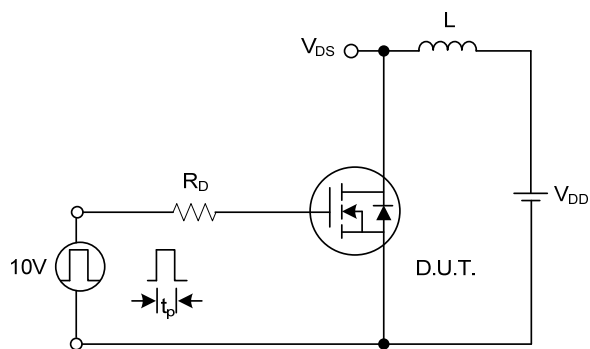
Switching Waveforms



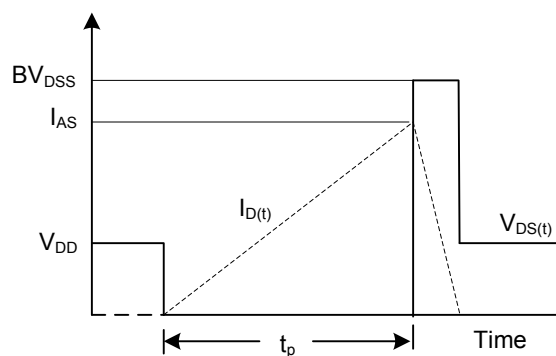
Gate Charge Test Circuit



Charge
Gate Charge Waveform



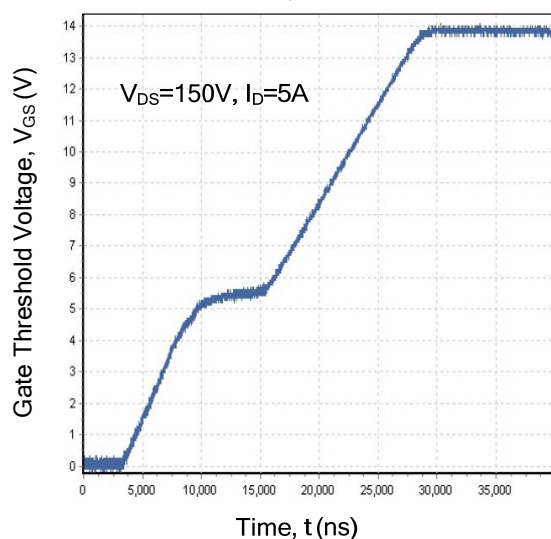
Unclamped Inductive Switching Test Circuit



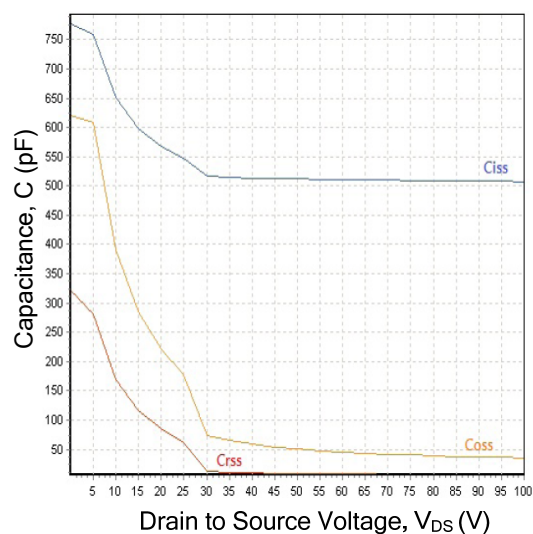
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

Gate-Charge Characteristics



Capacitance Characteristics



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